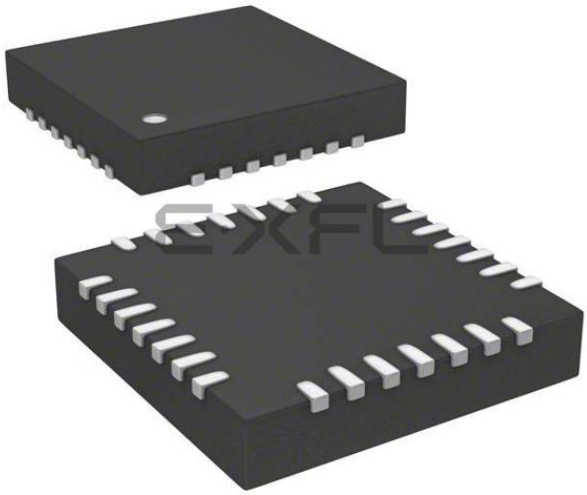

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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M0+
Core Size	32-Bit Single-Core
Speed	32MHz
Connectivity	I²C, IrDA, SPI, UART/USART
Peripherals	Brown-out Detect/Reset, DMA, POR, PWM, WDT
Number of I/O	24
Program Memory Size	16KB (16K x 8)
Program Memory Type	FLASH
EEPROM Size	512 x 8
RAM Size	2K x 8
Voltage - Supply (Vcc/Vdd)	1.65V ~ 3.6V
Data Converters	A/D 10x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	28-UFQFN
Supplier Device Package	28-UFQFPN (4x4)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32l021g4u6

1 Introduction

The ultra-low-power STM32L021x4 family includes devices in 6 different package types from 14 to 32 pins. The description below gives an overview of the complete range of peripherals proposed in this family.

These features make the ultra-low-power STM32L021x4 microcontrollers suitable for a wide range of applications:

- Gas/water meters and industrial sensors
- Healthcare and fitness equipment
- Remote control and user interface
- PC peripherals, gaming, GPS equipment
- Alarm system, wired and wireless sensors, video intercom

This STM32L021x4 datasheet should be read in conjunction with the STM32L0x1 reference manual (RM0377).

For information on the ARM® Cortex®-M0+ core please refer to the Cortex®-M0+ Technical Reference Manual, available from the www.arm.com website.

Figure 1 shows the general block diagram of the device family.

Table 4. Functionalities depending on the working mode (from Run/active down to standby) (continued)(1)(2)

IPs	Run/Active	Sleep	Low-power run	Low-power sleep	Stop	Standby
					Wakeup capability	Wakeup capability
Wakeup time to Run mode	0 µs	6 CPU cycles	3 µs	7 CPU cycles	5 µs	65 µs
Consumption V_{DD}=1.8 to 3.6 V (Typ)	Down to 128 µA/MHz (from Flash)	Down to 31 µA/MHz (from Flash)	Down to 7 µA	Down to 3.8 µA	0.29 µA (No RTC) V_{DD}=1.8 V	0.18 µA (No RTC) V_{DD}=1.8 V
					0.54 µA (with RTC) V_{DD}=1.8 V	0.41 µA (with RTC) V_{DD}=1.8 V
					0.34 µA (No RTC) V_{DD}=3.0 V	0.23 µA (No RTC) V_{DD}=3.0 V
					0.67 µA (with RTC) V_{DD}=3.0 V	0.53 µA (with RTC) V_{DD}=3.0 V

1. Legend:
   "Y" = Yes (enable).
   "O" = Optional, can be enabled/disabled by software)
   "-" = Not available
2. The consumption values given in this table are preliminary data given for indication. They are subject to slight changes.
3. Some peripherals with wakeup from Stop capability can request HSI to be enabled. In this case, HSI is woken up by the peripheral, and only feeds the peripheral which requested it. HSI is automatically put off when the peripheral does not need it anymore.
4. UART and LPUART reception is functional in Stop mode. It generates a wakeup interrupt on Start.To generate a wakeup on address match or received frame event, the LPUART can run on LSE clock while the UART has to wake up or keep running the HSI clock.
5. I2C address detection is functional in Stop mode. It generates a wakeup interrupt in case of address match. It will wake up the HSI during reception.

3.2 Interconnect matrix

Several peripherals are directly interconnected. This allows autonomous communication between peripherals, thus saving CPU resources and power consumption. In addition, these hardware connections allow fast and predictable latency.

Depending on peripherals, these interconnections can operate in Run, Sleep, Low-power run, Low-power sleep and Stop modes.

Table 5. STM32L021x4 peripherals interconnect matrix

Interconnect source	Interconnect destination	Interconnect action	Run	Sleep	Low-power run	Low-power sleep	Stop
COMPx	TIM2,TIM21	Timer input channel, trigger from analog signals comparison	Y	Y	Y	Y	-
	LPTIM1	Timer input channel, trigger from analog signals comparison	Y	Y	Y	Y	Y

Figure 2. Clock tree

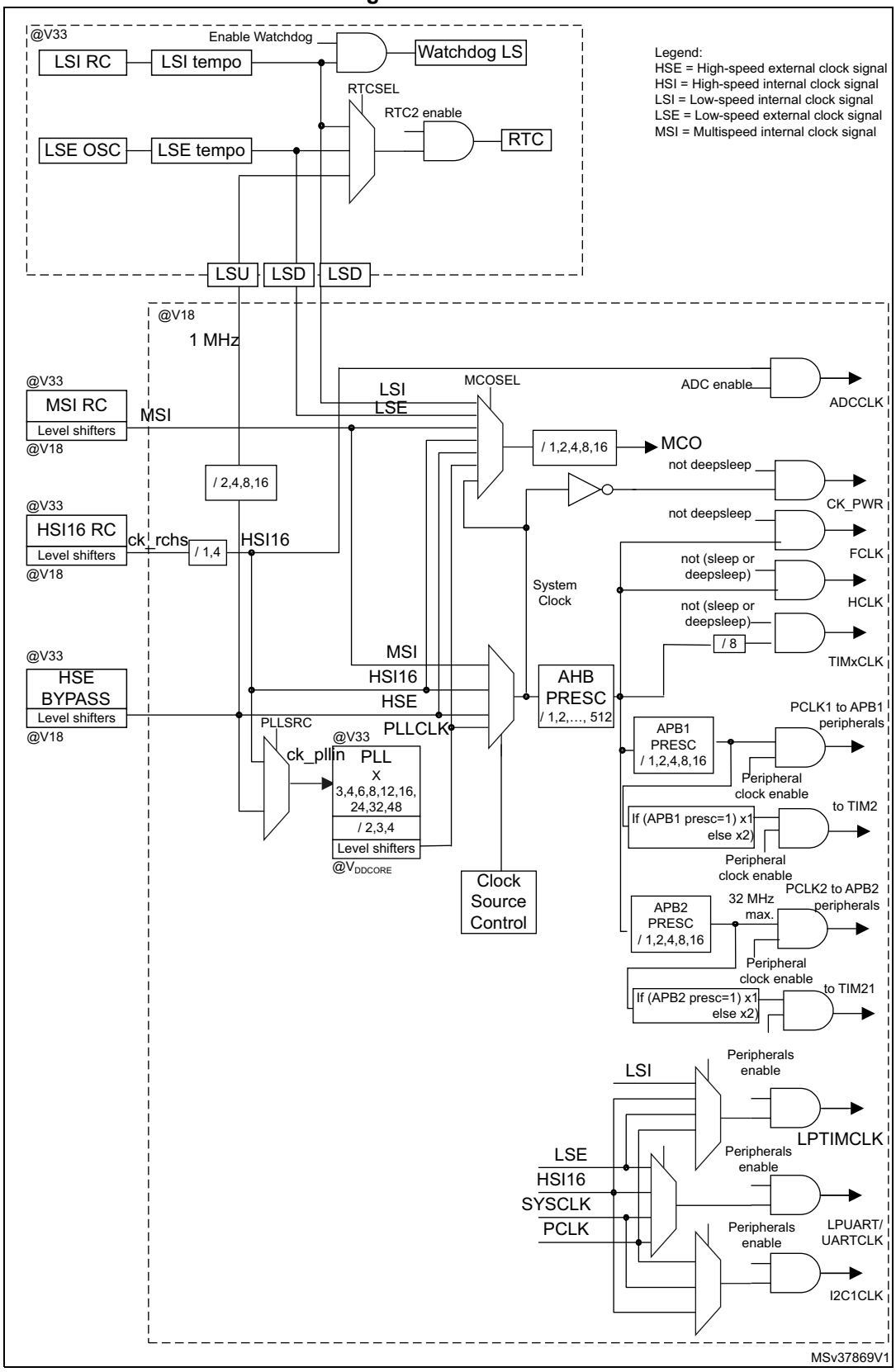
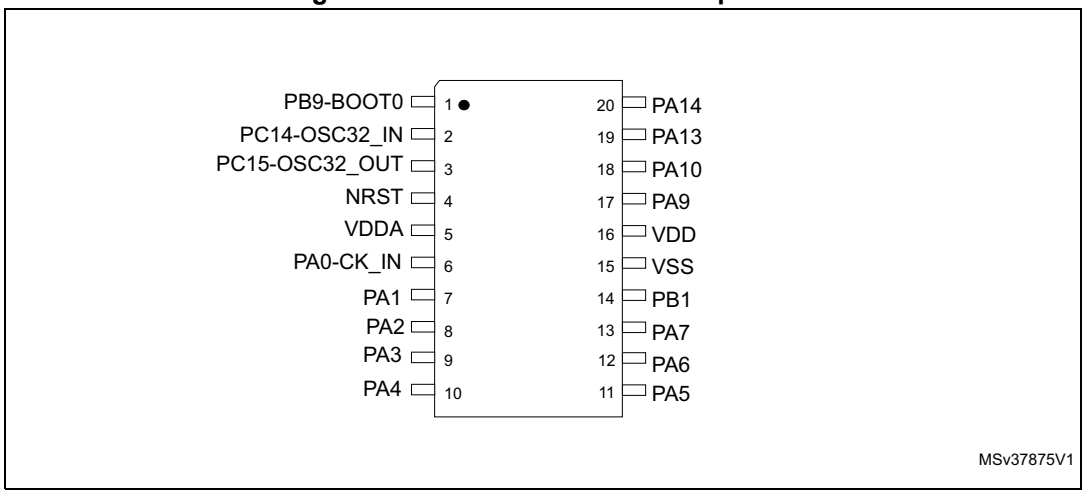
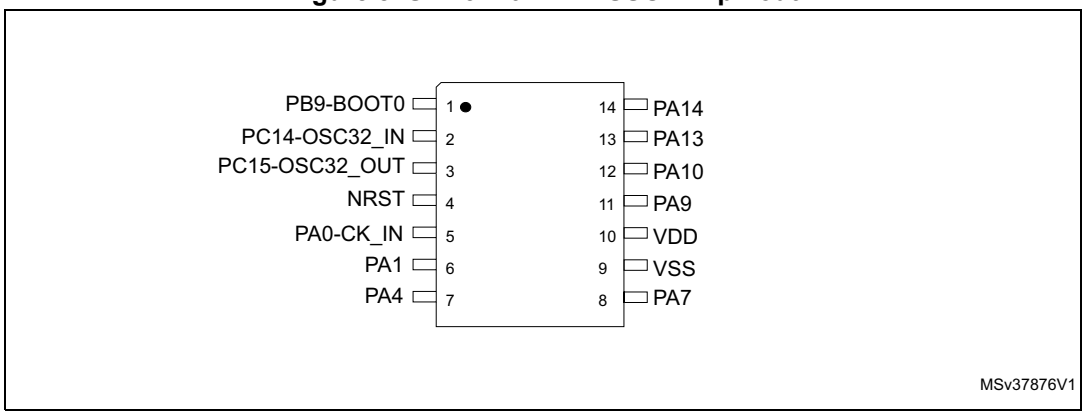


Figure 7. STM32L021x4 TSSOP20 pinout



1. The above figure shows the package top view.

Figure 8. STM32L021x4 TSSOP14 pinout



1. The above figure shows the package top view.

Table 11. Legend/abbreviations used in the pinout table

Name	Abbreviation	Definition
Pin name	Unless otherwise specified in brackets below the pin name, the pin function during and after reset is the same as the actual pin name	
Pin type	S	Supply pin
	I	Input only pin
	I/O	Input / output pin
I/O structure	FT	5 V tolerant I/O
	FTf	5 V tolerant I/O, FM+ capable
	TTa	3.3 V tolerant I/O directly connected to the ADC
	TC	Standard 3.3V I/O
	B	Dedicated BOOT0 pin
	RST	Bidirectional reset pin with embedded weak pull-up resistor

Table 12. Pin definitions (continued)

Pin number						Pin name (function after reset)	Pin type	I/O structure	Notes	Pin functions	
TSSOP14	UFQFPN20	TSSOP20	UFQFPN28	LQFP32	UFQFPN32[1]					Alternate functions	Additional functions
14	17	20	22	24	24	PA14	I/O	FT	-	SWCLK, LPTIM1_OUT, I2C1_SMBA, USART2_TX, SPI1_MISO, LPUART1_TX, COMP2_OUT	-
-	-	-	23	25	25	PA15	I/O	FT	-	SPI1_NSS, TIM2_ETR, EVENTOUT, USART2_RX, TIM2_CH1	-
-	-	-	24	26	26	PB3	I/O	FT	-	SPI1_SCK, TIM2_CH2, EVENTOUT	COMP2_INM
-	-	-	25	27	27	PB4	I/O	FT	-	SPI1_MISO, EVENTOUT	COMP2_INP
-	-	-	26	28	28	PB5	I/O	FT	-	SPI1_MOSI, LPTIM1_IN1, I2C1_SMBA, TIM21_CH1	COMP2_INP
-	18	-	27	29	29	PB6	I/O	FTf	-	USART2_TX, I2C1_SCL, LPTIM1_ETR, TIM2_CH3, LPUART1_TX	COMP2_INP
-	19	-	28	30	30	PB7	I/O	FTf	-	USART2_RX, I2C1_SDA, LPTIM1_IN2, TIM2_CH4, LPUART1_RX	COMP2_INP, VREF_PVD_IN
1	20	1	1	31	31	PB9-BOOT0	I	B	-	-	BOOT0 (Boot memory selection)
-	-	-	-	-	32	PB8	I/O	FTf	-	USART2_TX, EVENTOUT, I2C1_SCL, SPI1_NSS	-

6 Electrical characteristics

6.1 Parameter conditions

Unless otherwise specified, all voltages are referenced to V_{SS}.

6.1.1 Minimum and maximum values

Unless otherwise specified the minimum and maximum values are guaranteed in the worst conditions of ambient temperature, supply voltage and frequencies by tests in production on 100% of the devices with an ambient temperature at T_A = 25 °C and T_A = $T_A$max (given by the selected temperature range).

Data based on characterization results, design simulation and/or technology characteristics are indicated in the table footnotes and are not tested in production. Based on characterization, the minimum and maximum values refer to sample tests and represent the mean value plus or minus three times the standard deviation (mean±3σ).

6.1.2 Typical values

Unless otherwise specified, typical data are based on T_A = 25 °C, V_{DD} = 3.6 V (for the 1.65 V ≤ V_{DD} ≤ 3.6 V voltage range). They are given only as design guidelines and are not tested.

Typical ADC accuracy values are determined by characterization of a batch of samples from a standard diffusion lot over the full temperature range, where 95% of the devices have an error less than or equal to the value indicated (mean±2σ).

6.1.3 Typical curves

Unless otherwise specified, all typical curves are given only as design guidelines and are not tested.

6.1.4 Loading capacitor

The loading conditions used for pin parameter measurement are shown in *Figure 10*.

6.1.5 Pin input voltage

The input voltage measurement on a pin of the device is described in *Figure 11*.

Figure 10. Pin loading conditions

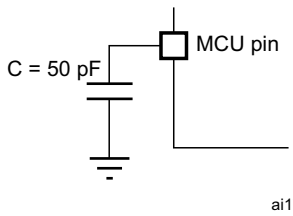
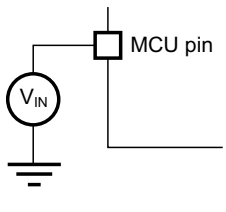


Figure 11. Pin input voltage



6.2 Absolute maximum ratings

Stresses above the absolute maximum ratings listed in *Table 14: Voltage characteristics*, *Table 15: Current characteristics*, and *Table 16: Thermal characteristics* may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these conditions is not implied. Exposure to maximum rating conditions for extended periods may affect device reliability.

Table 14. Voltage characteristics

Symbol	Ratings	Min	Max	Unit
V_{DD}–V_{SS}	External main supply voltage (including V_{DDA}, V_{DD})(1)	–0.3	4.0	V
V_{IN}(2)	Input voltage on FT and FTf pins	V_{SS} –0.3	V_{DD}+4.0	
	Input voltage on TC pins	V_{SS} –0.3	4.0	
	Input voltage on BOOT0	V_{SS}	V_{DD} +4.0	
	Input voltage on any other pin	V_{SS} –0.3	4.0	
$\lvert\Delta V_{DD}\rvert$	Variations between different V_{DDx} power pins	-	50	mV
$\lvert V_{DDA}-V_{DDx}\rvert$	Variations between any V_{DDx} and V_{DDA} power pins(3)	-	300	
$\lvert\Delta V_{SS}\rvert$	Variations between all different ground pins	-	50	
$V_{ESD(HBM)}$	Electrostatic discharge voltage (human body model)	see *Section 6.3.11*		

1. All main power (V_{DD}, V_{DDA}) and ground (V_{SS}, V_{SSA}) pins must always be connected to the external power supply, in the permitted range.
2. V_{IN} maximum must always be respected. Refer to *Table 15* for maximum allowed injected current values.
3. It is recommended to power V_{DD} and V_{DDA} from the same source. A maximum difference of 300 mV between V_{DD} and V_{DDA} can be tolerated during power-up and device operation. its value does not need to respect this rule.

Table 15. Current characteristics

Symbol	Ratings	Max.	Unit
ΣI_{VDD} (2)	Total current into sum of all V_{DD} power lines (source)(1)	105	mA
ΣI_{VSS} (2)	Total current out of sum of all V_{SS} ground lines (sink)(1)	105	
$I_{VDD(PIN)}$	Maximum current into each V_{DD} power pin (source)(1)	100	
$I_{VSS(PIN)}$	Maximum current out of each V_{SS} ground pin (sink)(1)	100	
I_{IO}	Output current sunk by any I/O and control pin except FTf pins	16	
	Output current sunk by FTf pins	22	
	Output current sourced by any I/O and control pin	-16	
$\Sigma I_{IO(PIN)}$ (3)	Total output current sunk by sum of all IOs and control pins(4)	45	
	Total output current sourced by sum of all IOs and control pins	-45	
$\Sigma I_{IO(PIN)}$	Total output current sunk by sum of all IOs and control pins(2)	90	
	Total output current sourced by sum of all IOs and control pins(2)	-90	
$I_{INJ(PIN)}$	Injected current on FT, FFf, RST and B pins	-5/+0(5)	
	Injected current on TC pin	± 5(6)	
$\Sigma I_{INJ(PIN)}$	Total injected current (sum of all I/O and control pins)(7)	± 25	

1. All main power (V_{DD}, V_{DDA}) and ground (V_{SS}, V_{SSA}) pins must always be connected to the external power supply, in the permitted range.
2. This current consumption must be correctly distributed over all I/Os and control pins. The total output current must not be sunk/sourced between two consecutive power supply pins referring to high pin count LQFP packages.
3. These values apply only to STM32L021GxUx part number (UFQFPN28 package).
4. This current consumption must be correctly distributed over all I/Os and control pins. In particular, it must be located the closest possible to the couple of supply and ground, and distributed on both sides.
5. Positive current injection is not possible on these I/Os. A negative injection is induced by $V_{IN}<V_{SS}$. $I_{INJ(PIN)}$ must never be exceeded. Refer to *Table 14* for maximum allowed input voltage values.
6. A positive injection is induced by $V_{IN} > V_{DD}$ while a negative injection is induced by $V_{IN} < V_{SS}$. $I_{INJ(PIN)}$ must never be exceeded. Refer to *Table 14: Voltage characteristics* for the maximum allowed input voltage values.
7. When several inputs are submitted to a current injection, the maximum $\Sigma I_{INJ(PIN)}$ is the absolute sum of the positive and negative injected currents (instantaneous values).

Table 16. Thermal characteristics

Symbol	Ratings	Value	Unit
T_{STG}	Storage temperature range	–65 to +150	°C
T_J	Maximum junction temperature	150	°C

Table 18. Embedded reset and power control block characteristics (continued)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{BOR3}	Brown-out reset threshold 3	Falling edge	2.45	2.55	2.6	V
		Rising edge	2.54	2.66	2.7	
V_{BOR4}	Brown-out reset threshold 4	Falling edge	2.68	2.8	2.85	
		Rising edge	2.78	2.9	2.95	
V_{PVD0}	Programmable voltage detector threshold 0	Falling edge	1.8	1.85	1.88	
		Rising edge	1.88	1.94	1.99	
V_{PVD1}	PVD threshold 1	Falling edge	1.98	2.04	2.09	
		Rising edge	2.08	2.14	2.18	
V_{PVD2}	PVD threshold 2	Falling edge	2.20	2.24	2.28	
		Rising edge	2.28	2.34	2.38	
V_{PVD3}	PVD threshold 3	Falling edge	2.39	2.44	2.48	
		Rising edge	2.47	2.54	2.58	
V_{PVD4}	PVD threshold 4	Falling edge	2.57	2.64	2.69	
		Rising edge	2.68	2.74	2.79	
V_{PVD5}	PVD threshold 5	Falling edge	2.77	2.83	2.88	
		Rising edge	2.87	2.94	2.99	
V_{PVD6}	PVD threshold 6	Falling edge	2.97	3.05	3.09	
		Rising edge	3.08	3.15	3.20	
V_{hyst}	Hysteresis voltage	BOR0 threshold	-	40	-	mV
		All BOR and PVD thresholds excepting BOR0	-	100	-	

1. Guaranteed by characterization results, not tested in production.
2. Valid for device version without BOR at power up. Please see option "D" in Ordering information scheme for more details.

Table 23. Current consumption in Run mode, code with data processing running from RAM

Symbol	Parameter	Conditions		f_{HCLK}	Typ	Max(1)	Unit
I_{DD} (Run from RAM)	Supply current in Run mode, code executed from RAM, Flash switched OFF	$f_{HSE} = f_{HCLK}$ up to 16 MHz, included $f_{HSE} = f_{HCLK}/2$ above 16 MHz (PLL ON)(2)	Range 3, V_{CORE}=1.2 V, VOS[1:0]=11	1 MHz	115	140	µA
				2 MHz	205	240	
				4 MHz	385	420	
			Range 2, V_{CORE}=1.5 ,V, VOS[1:0]=10	4 MHz	0.48	0.55	mA
				8 MHz	0.935	1.1	
				16 MHz	1.8	2	
			Range 1, V_{CORE}=1.8 V, VOS[1:0]=01	8 MHz	1.1	1.4	
				16 MHz	2.1	2.5	
				32 MHz	4.5	4.9	
		MSI clock	Range 3, V_{CORE}=1.2 V, VOS[1:0]=11	65 kHz	22	38	µA
				524 kHz	67	91	
				4.2 MHz	415	450	
		HSI16 clock source (16 MHz)	Range 2, V_{CORE}=1.5 V, VOS[1:0]=10	16 MHz	1.95	2.2	mA
			Range 1, V_{CORE}=1.8 V, VOS[1:0]=01	32 MHz	4.7	5.2	

1. Guaranteed by characterization results at 125 °C, not tested in production, unless otherwise specified.
2. Oscillator bypassed (HSEBYP = 1 in RCC_CR register).

Table 24. Current consumption in Run mode vs code type, code with data processing running from RAM(1)

Symbol	Parameter	Conditions			f_{HCLK}	Typ	Unit
I_{DD} (Run from RAM)	Supply current in Run mode, code executed from RAM, Flash switched OFF	$f_{HSE} = f_{HCLK}$ up to 16 MHz, included, $f_{HSE} = f_{HCLK}/2$ above 16 MHz (PLL ON)(2)	Range 3, V_{CORE}=1.2 V, VOS[1:0]=11	Dhrystone	4 MHz	385	µA
				CoreMark		-(3)	
				Fibonacci		350	
				while(1)		340	
			Range 1, V_{CORE}=1.8 V, VOS[1:0]=01	Dhrystone	32 MHz	4.5	mA
				CoreMark		-(3)	
				Fibonacci		4.2	
				while(1)		3	

1. Guaranteed by characterization results, not tested in production, unless otherwise specified.
2. Oscillator bypassed (HSEBYP = 1 in RCC_CR register).
3. CoreMark code is unable to run from RAM since the RAM size is only 2 Kbytes.

Table 25. Current consumption in Sleep mode

Symbol	Parameter	Conditions		f_{HCLK}	Typ	Max(1)	Unit
I_{DD} (Sleep)	Supply current in Sleep mode, Flash OFF	f_{HSE} = f_{HCLK} up to 16 MHz included, f_{HSE} = f_{HCLK}/2 above 16 MHz (PLL ON)(2)	Range 3, V_{CORE}=1.2 V, VOS[1:0]=11	1 MHz	36.5	70	µA
				2 MHz	58	95	
				4 MHz	100	150	
			Range 2, V_{CORE}=1.5 V, VOS[1:0]=10	4 MHz	125	170	
				8 MHz	230	300	
				16 MHz	450	540	
			Range 1, V_{CORE}=1.8 V, VOS[1:0]=01	8 MHz	275	350	
				16 MHz	555	650	
				32 MHz	1350	1600	
		MSI clock	Range 3, V_{CORE}=1.2 V, VOS[1:0]=11	65 kHz	15.5	32	
				524 kHz	26.5	55	
				4.2 MHz	115	160	
		HSI16 clock source (16 MHz)	Range 2, V_{CORE}=1.5 V, VOS[1:0]=10	16 MHz	585	670	
			Range 1, V_{CORE}=1.8 V, VOS[1:0]=01	32 MHz	1500	1700	
	Supply current in Sleep mode, Flash ON	f_{HSE} = f_{HCLK} up to 16 MHz included, f_{HSE} = f_{HCLK}/2 above 16 MHz (PLL ON)(2)	Range 3, V_{CORE}=1.2 V, VOS[1:0]=11	1 MHz	49	88	
				2 MHz	69	120	
				4 MHz	115	190	
			Range 2, CORE=1.5 V, VOS[1:0]=10	4 MHz	135	200	
				8 MHz	240	340	
				16 MHz	460	650	
			Range 1, V_{CORE}=1.8 V, VOS[1:0]=01	8 MHz	290	400	
				16 MHz	565	750	
				32 MHz	1350	1900	
		MSI clock	Range 3, V_{CORE}=1.2 V, VOS[1:0]=11	65 kHz	26.5	46	
				524 kHz	38.5	70	
				4.2 MHz	125	190	
		HSI16 clock source (16 MHz)	Range 2, V_{CORE}=1.5 V, VOS[1:0]=10	16 MHz	600	760	
			Range 1, V_{CORE}=1.8 V, VOS[1:0]=01	32 MHz	1500	1850	

1. Guaranteed by characterization results at 125 °C, not tested in production, unless otherwise specified.
2. Oscillator bypassed (HSEBYP = 1 in RCC_CR register).

6.3.7 Internal clock source characteristics

The parameters given in *Table 37* are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in *Table 17*.

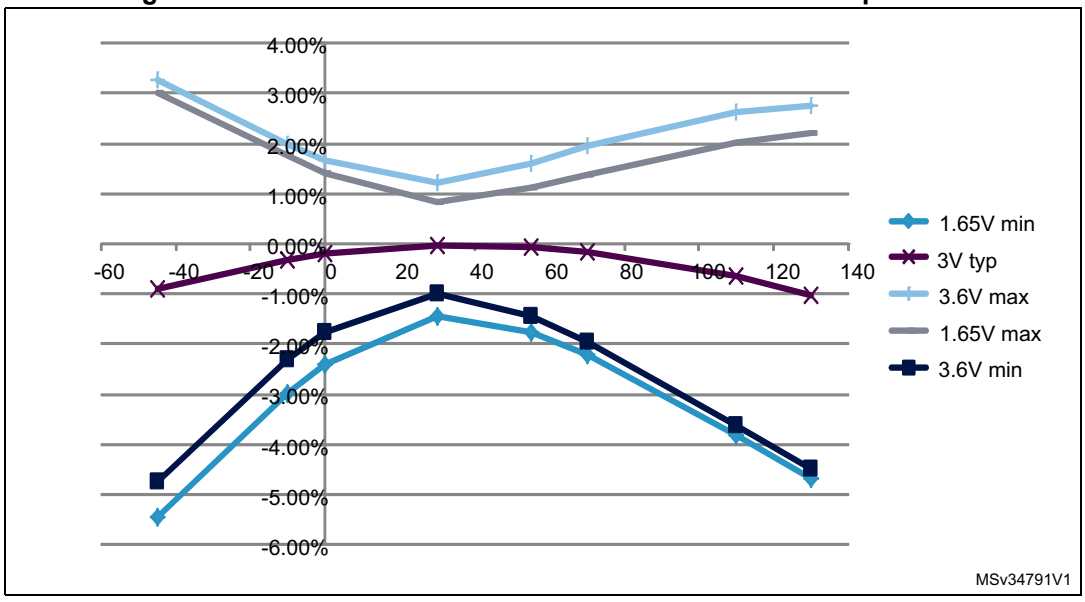
High-speed internal 16 MHz (HSI16) RC oscillator

Table 37. 16 MHz HSI16 oscillator characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{HSI16}	Frequency	V_{DD} = 3.0 V	-	16	-	MHz
$TRIM^{(1)(2)}$	HSI16 user-trimmed resolution	Trimming code is not a multiple of 16	-	±0.4	0.7	%
		Trimming code is a multiple of 16	-	-	±1.5	%
ACC_{HSI16} (2)	Accuracy of the factory-calibrated HSI16 oscillator	V_{DDA} = 3.0 V, T_A = 25 °C	-1(3)	-	1(3)	%
		V_{DDA} = 3.0 V, T_A = 0 to 55 °C	-1.5	-	1.5	%
		V_{DDA} = 3.0 V, T_A = -10 to 70 °C	-2	-	2	%
		V_{DDA} = 3.0 V, T_A = -10 to 85 °C	-2.5	-	2	%
		V_{DDA} = 3.0 V, T_A = -10 to 105 °C	-4	-	2	%
		V_{DDA} = 1.65 V to 3.6 V T_A = -40 to 125 °C	-5.45	-	3.25	%
$t_{SU(HSI16)}^{(2)}$	HSI16 oscillator startup time	-	-	3.7	6	µs
$I_{DD(HSI16)}^{(2)}$	HSI16 oscillator power consumption	-	-	100	140	µA

1. The trimming step differs depending on the trimming code. It is usually negative on the codes which are multiples of 16 (0x00, 0x10, 0x20, 0x30...0xE0).
2. Guaranteed by characterization results, not tested in production.
3. Guaranteed by test in production.

Figure 22. HSI16 minimum and maximum value versus temperature



Input/output AC characteristics

The definition and values of input/output AC characteristics are given in *Figure 25* and *Table 51*, respectively.

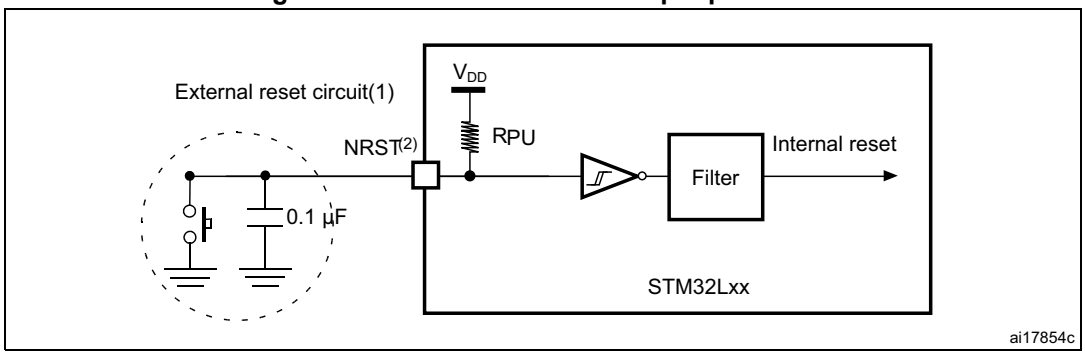
Unless otherwise specified, the parameters given in *Table 51* are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in *Table 17*.

Table 51. I/O AC characteristics(1)(2)

OSPEEDRx [1:0] bit value(1)	Symbol	Parameter	Conditions	Min	Max(3)	Unit
00	$f_{max(IO)out}$	Maximum frequency(4)	C_L = 50 pF, V_{DD} = 2.7 V to 3.6 V	-	400	kHz
			C_L = 50 pF, V_{DD} = 1.65 V to 2.7 V	-	100	
	$t_{f(IO)out}$ $t_{r(IO)out}$	Output rise and fall time	C_L = 50 pF, V_{DD} = 2.7 V to 3.6 V	-	125	ns
			C_L = 50 pF, V_{DD} = 1.65 V to 2.7 V	-	320	
01	$f_{max(IO)out}$	Maximum frequency(4)	C_L = 50 pF, V_{DD} = 2.7 V to 3.6 V	-	2	MHz
			C_L = 50 pF, V_{DD} = 1.65 V to 2.7 V	-	0.6	
	$t_{f(IO)out}$ $t_{r(IO)out}$	Output rise and fall time	C_L = 50 pF, V_{DD} = 2.7 V to 3.6 V	-	30	ns
			C_L = 50 pF, V_{DD} = 1.65 V to 2.7 V	-	65	
10	$F_{max(IO)out}$	Maximum frequency(4)	C_L = 50 pF, V_{DD} = 2.7 V to 3.6 V	-	10	MHz
			C_L = 50 pF, V_{DD} = 1.65 V to 2.7 V	-	2	
	$t_{f(IO)out}$ $t_{r(IO)out}$	Output rise and fall time	C_L = 50 pF, V_{DD} = 2.7 V to 3.6 V	-	13	ns
			C_L = 50 pF, V_{DD} = 1.65 V to 2.7 V	-	28	
11	$F_{max(IO)out}$	Maximum frequency(4)	C_L = 30 pF, V_{DD} = 2.7 V to 3.6 V	-	35	MHz
			C_L = 50 pF, V_{DD} = 1.65 V to 2.7 V	-	10	
	$t_{f(IO)out}$ $t_{r(IO)out}$	Output rise and fall time	C_L = 30 pF, V_{DD} = 2.7 V to 3.6 V	-	6	ns
			C_L = 50 pF, V_{DD} = 1.65 V to 2.7 V	-	17	
-	t_{EXTIpw}	Pulse width of external signals detected by the EXTI controller	-	8	-	ns

1. The I/O speed is configured using the OSPEEDRx[1:0] bits. Refer to the line reference manual for a description of GPIO Port configuration register.
2. BOOT0/PB9 maximum input frequency is 10 kHz (1.65 V < V_{DD} < 2.7 V) and 5 MHz (2.7 V < V_{DD} < 3.6 V).
3. Guaranteed by design. Not tested in production.
4. The maximum frequency is defined in *Figure 25*.

Figure 26. Recommended NRST pin protection



1. The reset network protects the device against parasitic resets.
2. The user must ensure that the level on the NRST pin can go below the $V_{IL(NRST)}$ max level specified in *Table 52*. Otherwise the reset will not be taken into account by the device.

6.3.15 12-bit ADC characteristics

Unless otherwise specified, the parameters given in *Table 53* are values derived from tests performed under ambient temperature, f_{PCLK} frequency and V_{DDA} supply voltage conditions summarized in *Table 17: General operating conditions*.

Note: It is recommended to perform a calibration after each power-up.

Table 53. ADC characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DDA}	Analog supply voltage for ADC ON	Fast channel	1.65	-	3.6	V
		Standard channels	1.75(1)	-	3.6	
$I_{DDA\ (ADC)}$	Current consumption of the ADC on V_{DDA}	1.14 Msps	-	200	-	µA
		10 ksps	-	40	-	
	Current consumption of the ADC on V_{DD}(2)	1.14 Msps	-	70	-	
		10 ksps	-	1	-	
f_{ADC}	ADC clock frequency	Voltage scaling Range 1	0.14	-	16	MHz
		Voltage scaling Range 2	0.14	-	8	
		Voltage scaling Range 3	0.14	-	4	
f_S(3)	Sampling rate	-	0.05	-	1.14	MHz
f_{TRIG}(3)	External trigger frequency	f_{ADC} = 16 MHz, 16-bit resolution	-	-	941	kHz
		-	-	-	17	$1/f_{ADC}$
V_{AIN}	Conversion voltage range	-	0	-	V_{DDA}	V
R_{AIN}(3)	External input impedance	See *Equation 1* and *Table 54* for details	-	-	50	kΩ
R_{ADC}(3)(4)	Sampling switch resistance	-	-	-	1	kΩ
C_{ADC}(3)	Internal sample and hold capacitor	-	-	-	8	pF

Table 65. SPI characteristics in voltage Range 2 (1)

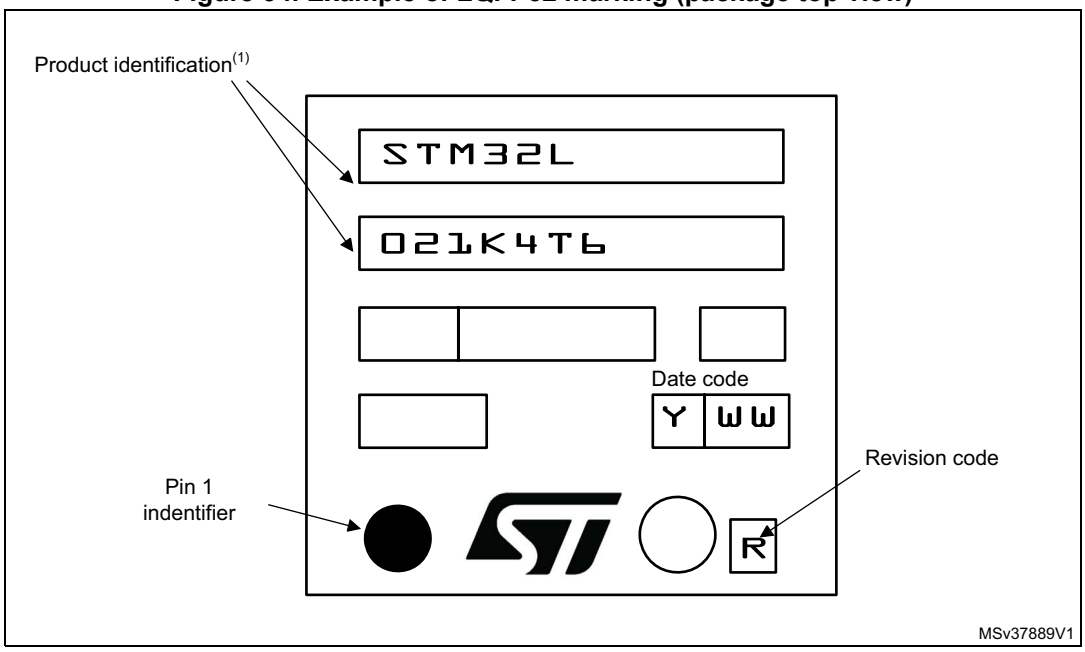
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{SCK} $1/t_{c(SCK)}$	SPI clock frequency	Master mode	-	-	8	MHz
		Slave mode Transmitter $1.65<V_{DD}<3.6V$			8	
		Slave mode Transmitter $2.7<V_{DD}<3.6V$			8(2)	
$Duty_{(SCK)}$	Duty cycle of SPI clock frequency	Slave mode	30	50	70	%
$t_{su(NSS)}$	NSS setup time	Slave mode, SPI presc = 2	4Tpclk	-	-	ns
$t_{h(NSS)}$	NSS hold time	Slave mode, SPI presc = 2	2Tpclk	-	-	
$t_{w(SCKH)}$ $t_{w(SCKL)}$	SCK high and low time	Master mode	Tpclk-2	Tpclk	Tpclk+2	
$t_{su(MI)}$	Data input setup time	Master mode	3	-	-	
$t_{su(SI)}$		Slave mode	3	-	-	
$t_{h(MI)}$	Data input hold time	Master mode	6	-	-	
$t_{h(SI)}$		Slave mode	2	-	-	
$t_{a(SO}$	Data output access time	Slave mode	18	-	52	
$t_{dis(SO)}$	Data output disable time	Slave mode	12	-	42	
$t_{v(SO)}$	Data output valid time	Slave mode	-	16	33	
		Master mode	-	4	6	
$t_{v(MO)}$	Data output hold time	Slave mode	11	-	-	
$t_{h(SO)}$		Master mode	3	-	-	

1. Guaranteed by characterization results, not tested in production.
2. The maximum SPI clock frequency in slave transmitter mode is determined by the sum of $t_{v(SO)}$ and $t_{su(MI)}$ which has to fit into SCK low or high phase preceding the SCK sampling edge. This value can be achieved when the SPI communicates with a master having $t_{su(MI)}$ = 0 while $Duty_{(SCK)}$ = 50%.

LQFP32 device marking

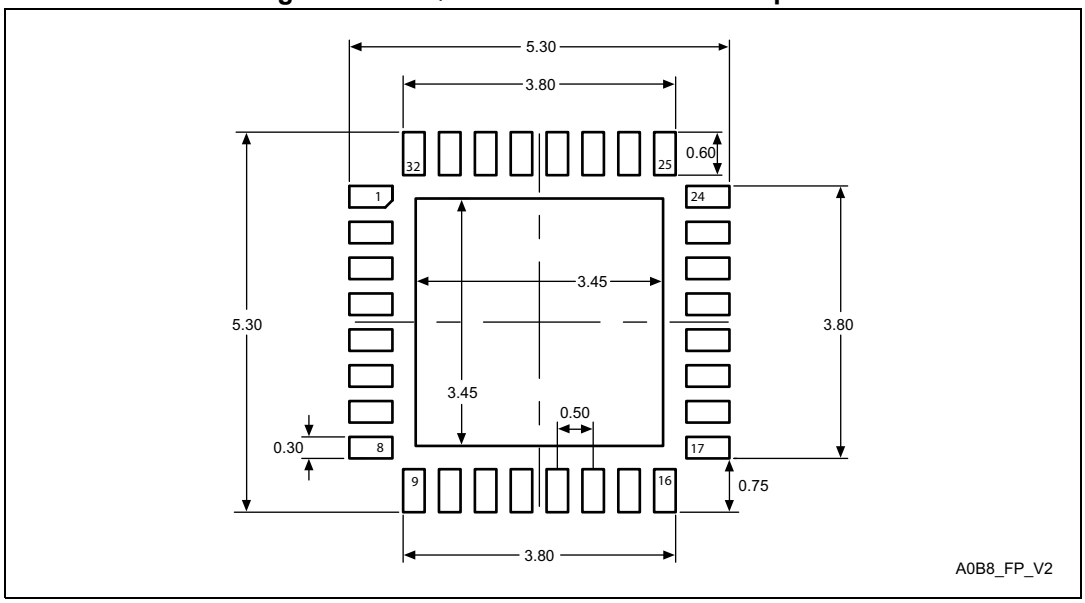
The following figure gives an example of topside marking versus pin 1 position identifier location.

Figure 34. Example of LQFP32 marking (package top view)



1. Parts marked as “ES”, “E” or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering samples to run qualification activity.

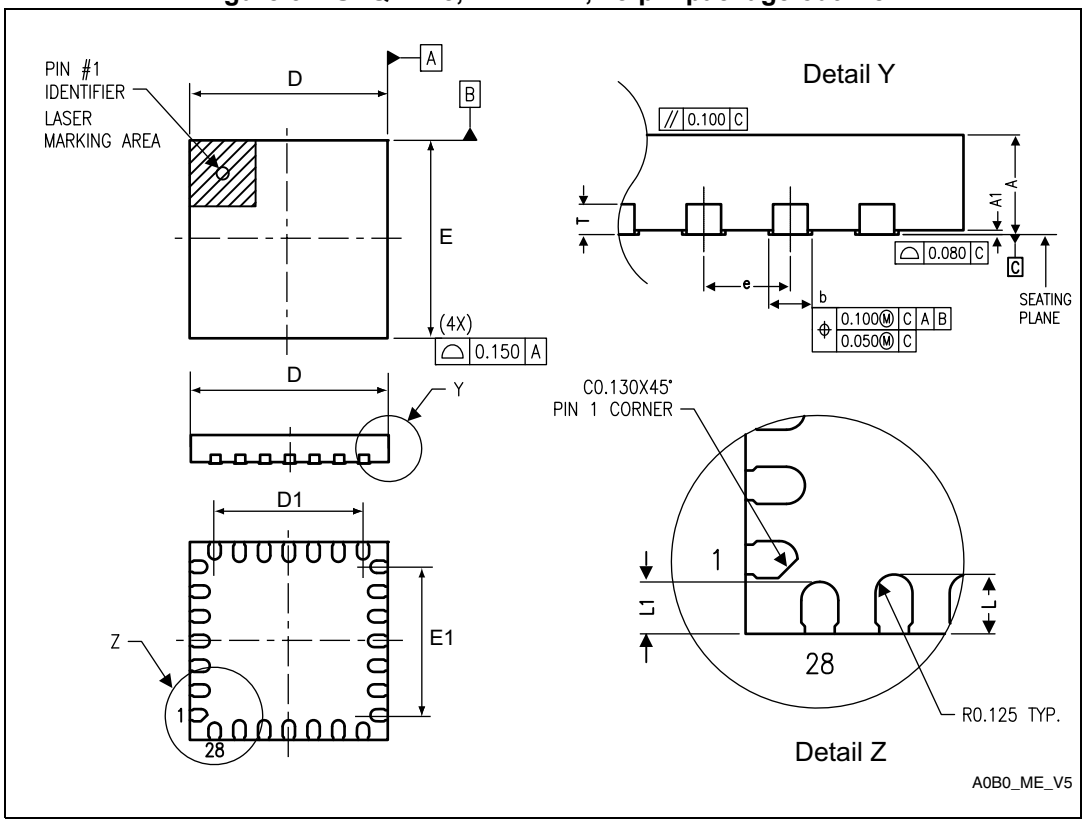
Figure 36. UFQFPN32 recommended footprint



1. Dimensions are expressed in millimeters.

7.3 UFQFPN28 4 x 4 mm package information

Figure 37. UFQPN28, 4 x 4 mm, 28-pin package outline

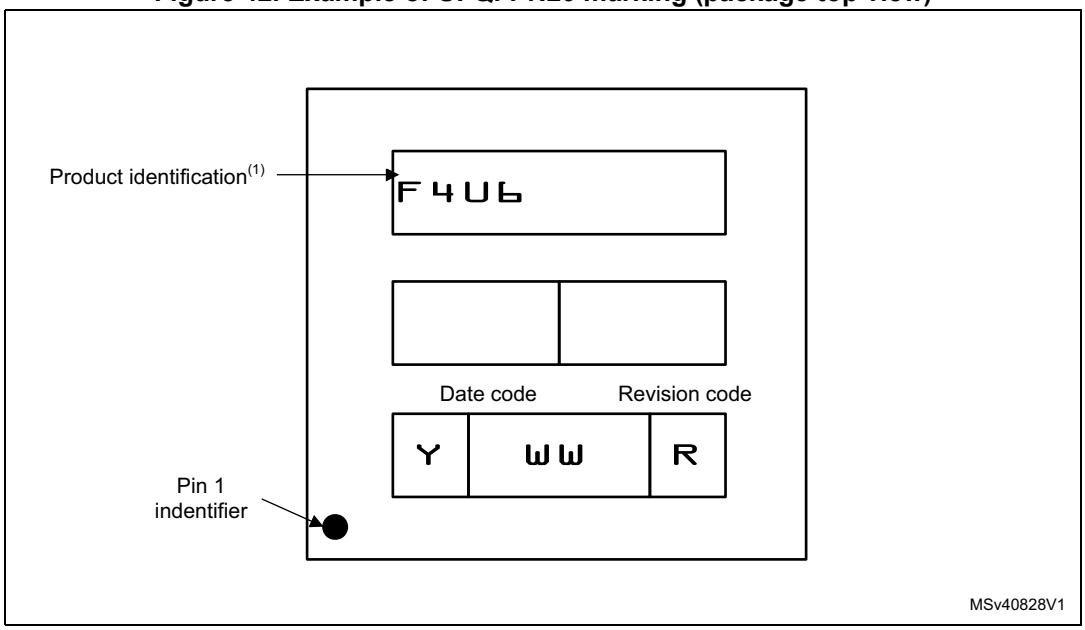


1. Drawing is not to scale.

UFQFPN20 device marking

The following figure gives an example of topside marking versus pin 1 position identifier location.

Figure 42. Example of UFQFPN20 marking (package top view)



1. Parts marked as “ES”, “E” or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering samples to run qualification activity.